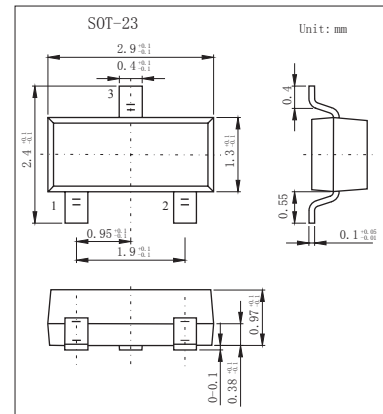
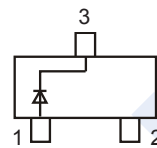


Schottky Diodes

1SS349

■ Features

- Small package
- Low forward voltage: $V_{F3} = 0.49V$ (Typ).
- Low voltage current: $I_R = 50 \mu A$ (Max).

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Maximum(Peak) Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V_R	20	V
Average Rectified Forward Current	I_o	1000	mA
Maximum(Peak) Forward Current	I_{FM}	3000	mA
Power Dissipation	P	200	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ C$
Operating Poerating Temperature Range	T_{opr}	-40 to +100	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu A$	20			V
Forward voltage	V_{F1}	$I_F = 100 mA$		0.34		
	V_{F2}	$I_F = 500 mA$		0.42		
	V_{F3}	$I_F = 1000 mA$		0.49	0.55	
Reverse voltage leakage current	I_R	$V_R = 20 V$			50	μA
Capacitance between terminals	C_T	$V_R = 0 V, f = 1 MHz$		250		pF

■ Marking

Marking	L9
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■ Typical Characteristics

